Amendments to the Specification:

Please amend the paragraph (section) beginning on page 5, at line 9 as shown below:

By contrast, in the present invention it is not the rate of flow, but rather it is the direction of flow, which plays the decisive role. When pulling a silicon single crystal with a diameter of at least 200 mm out of a crucible with a diameter of at least 450 mm, with a traveling magnetic field applied with its force directed downward (first embodiment of the invention), the direction of flow is no longer directed upward, toward the surface of the melt. Rather, convection is established, which is initially directed toward the ~~base~~ bottom of the crucible and later toward the growing single crystal. As a result, oxygen is included in the growing silicon single crystal at a virtually constant rate. This occurs even though a crucible promotes the evaporation of SiO out of the melt, since it allows a relatively large open surface of the melt to be used.